



# SMT8N60

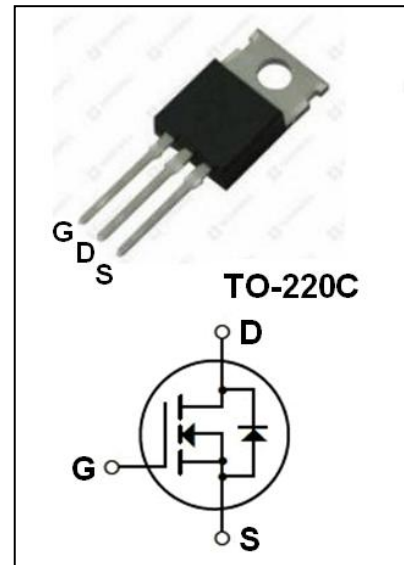
600V N-Channel MOSFET

### ●Features:

- 8.0A, 600V,  $R_{DS(on)(Typ)} = 1.0\Omega @ V_{GS}=10V$
- Low Gate Charge
- Low  $C_{rSS}$
- 100% Avalanche Tested
- Fast Switching
- Improved dv/dt Capability

### ●Application:

- High Frequency Switching Mode Power Supply
- Active Power Factor Correction



### Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain-Source Voltage	600	V
$I_D$	Drain Current - Continuous ( $T_c=25^\circ\text{C}$ ) - Continuous ( $T_c=100^\circ\text{C}$ )	8.0*	A
		5.1*	A
$I_{DM}$	Drain Current -Pulsed (Note1)	32*	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note2)	600	mJ
$I_{AR}$	Avalanche Current (Note1)	8.0	A
$E_{AR}$	Repetitive Avalanche Energy (Note1)	15.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_c = 25^\circ\text{C}$ ) -Derate above $25^\circ\text{C}$	116	W
		0.93	W/ $^\circ\text{C}$
$T_j$	Operating Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

\* Drain Current Limited by Maximum Junction Temperature.

### Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.07	$^\circ\text{C} / \text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ\text{C} / \text{W}$



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### Electrical Characteristics(Tc=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	600	--	--	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250μA (Referenced to 25°C)	--	0.7	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V	--	--	1	μA
		V <sub>DS</sub> =480V, Tc=125°C	--	--	10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> =+30V, V <sub>DS</sub> =0V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> =-30V, V <sub>DS</sub> =0V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	--	4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10 V, I <sub>D</sub> =4.0A	--	1.0	1.2	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =40 V, I <sub>D</sub> =4.0A (Note4)	--	7	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	--	1400	--	pF
C <sub>oss</sub>	Output Capacitance		--	175	--	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	16	--	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 8.0 A, R <sub>G</sub> = 25 Ω (Note4,5)	--	13.5	--	ns
t <sub>r</sub>	Turn-On Rise Time		--	105	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	128	--	ns
t <sub>f</sub>	Turn-Off Fall Time		--	49	--	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 480 V, I <sub>D</sub> =8.0 A, V <sub>GS</sub> = 10 V (Note4,5)	--	31	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	6.5	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	14.7	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	8.0	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	32	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =8.0A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> =0V, I <sub>S</sub> =8.0A, d I <sub>F</sub> /dt=100A/μs (Note4)	--	325	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	2.7	--	μC

Notes:

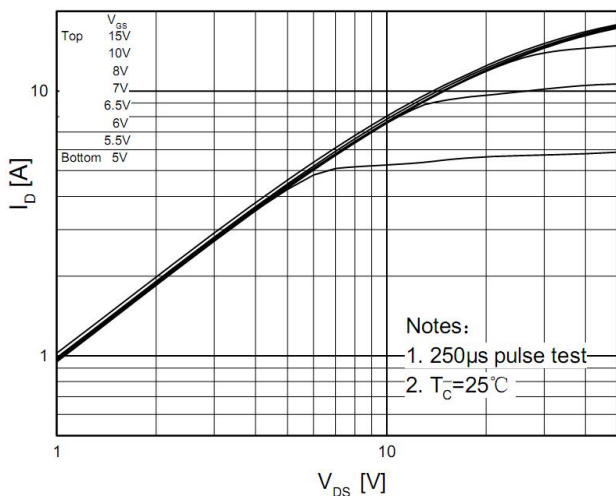
- 1、Repetitive Rating:Pulse Width Limited by Maximum Junction Temperature.
- 2、L = 18.5mH, I<sub>AS</sub> =8.0A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C.
- 3、I<sub>SD</sub>≤8.0A, di/dt≤200A/μs, V<sub>DD</sub>≤BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C.
- 4、Pulse Test : Pulse Width ≤300 μ s, Duty Cycle≤2%.
- 5、Essentially Independent of Operating Temperature.



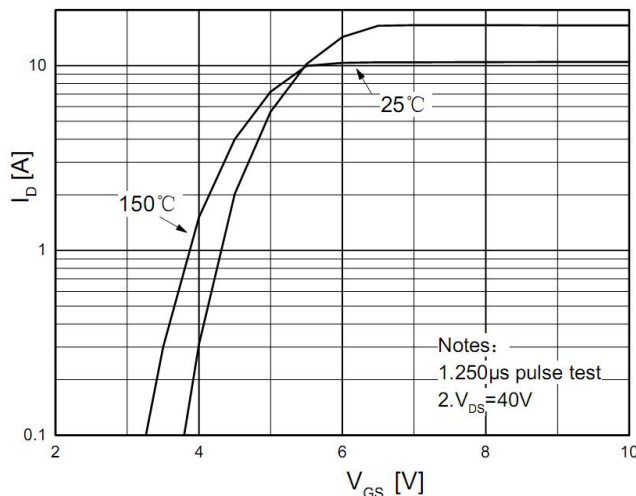
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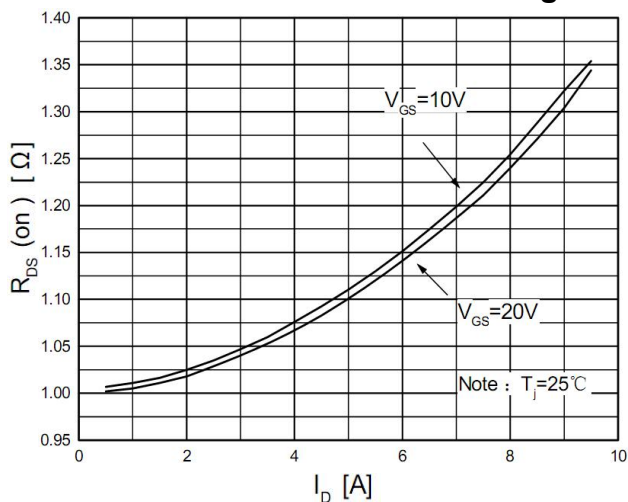
### On-Regin Characteristics



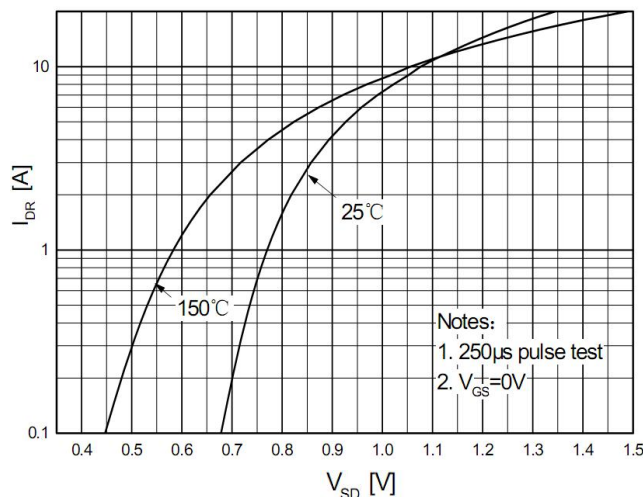
### Transfer Characteristics



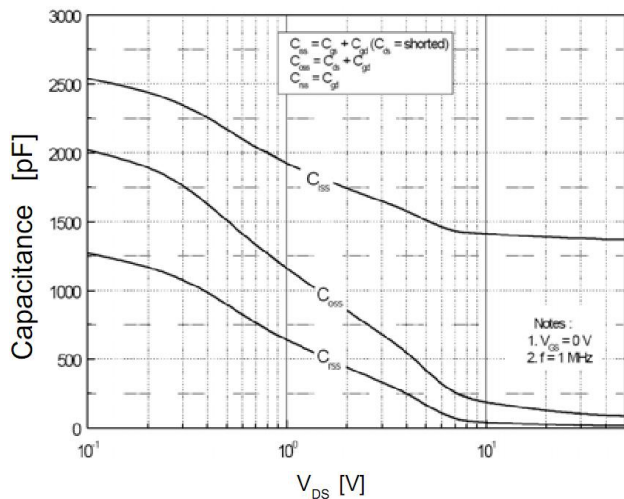
### On-Resistance Variation vs. Drain Current and Gate Voltage



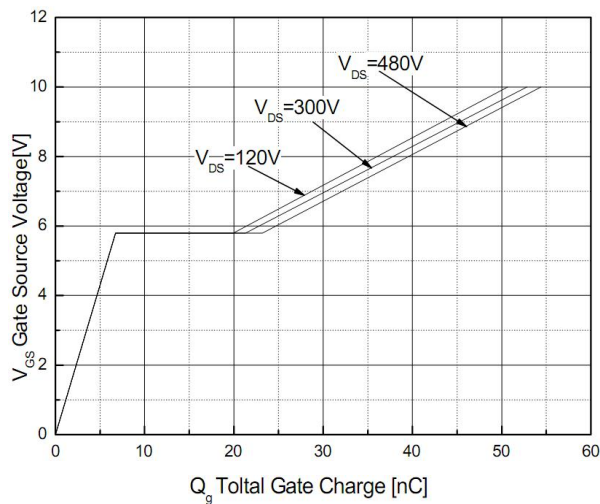
### Body Diode Forward Voltage Variation vs. Source Current and Temperature



### Capacitance Characteristics



### Gate Charge Characteristics

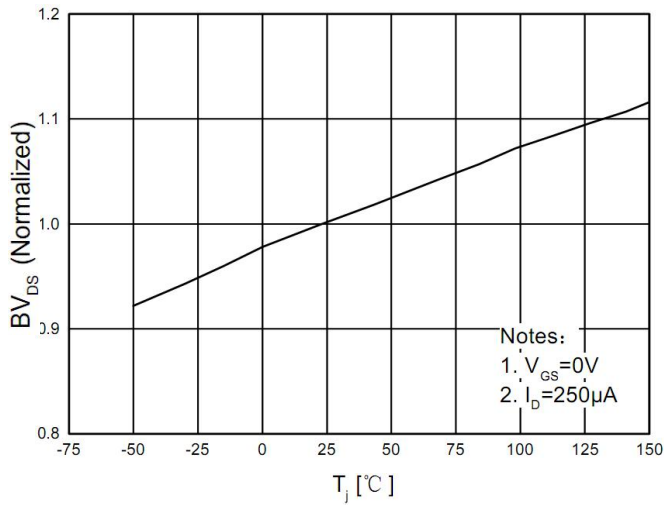




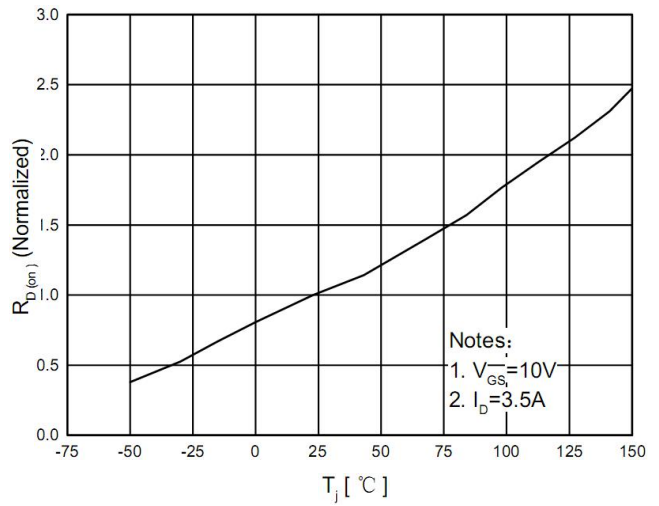
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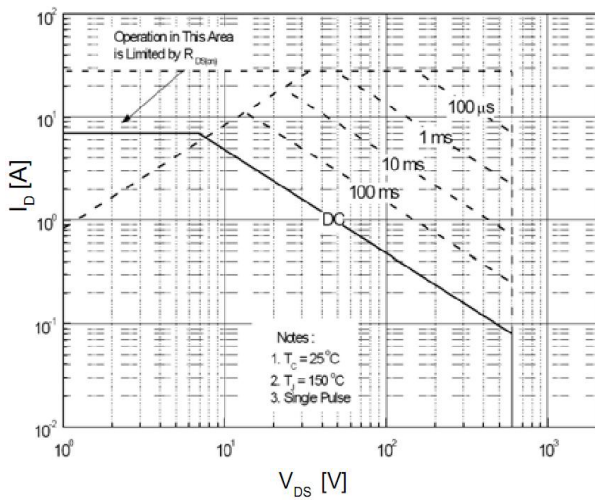
### Breakdown Voltage Variation vs. Temperature



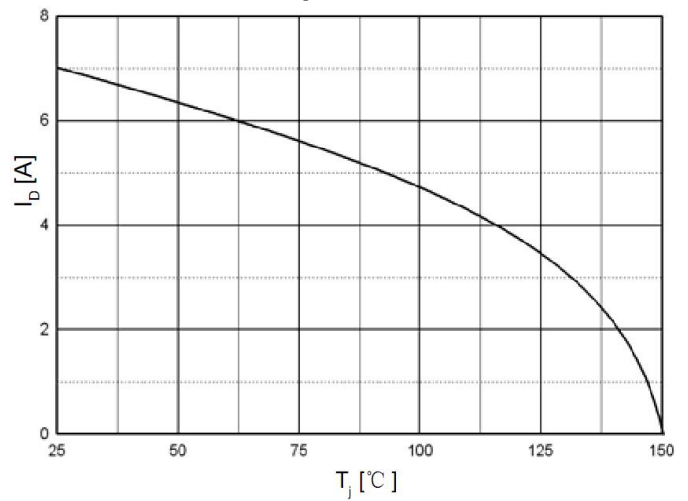
### On-Resistance Variation vs. Temperature



### Maximum Safe Operating Area



### Maximum Drain Current Vs. Case Temperature



**TO-220 MECHANICAL DATA**

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	4.00		4.80	E	9.50		10.50
B	1.25		1.55	e		2.54	
B1	0.55		1.05	F	1.15		1.45
b1	0.65		0.95	L	12.00		14.00
c	0.40		0.60	L1	2.50	3.00	3.50
D	14.80		16.80	Q	2.50		3.50
D1	6.00		7.00	Q1	1.80		2.80
				$\phi P$	3.40		3.90

